

Sample &

High Efficiency Boost Converter

1 General Description

The RT4812 allows systems to take advantage of new battery chemistries that can supply significant energy even when the battery voltage is lower than the required voltage for system power ICs. By combining built-in power transistors, synchronous rectification, and low supply current, this IC provides a compact solution for systems using advanced Li-lon battery chemistries.

The RT4812 is a boost regulator designed to provide a minimum output voltage from a single-cell Li-lon battery, even when the battery voltage is below system minimum. In boost mode, output voltage regulation is guaranteed up to a maximum load current of 2.1A. Quiescent current in Shutdown Mode is less than 1µA, which maximizes battery life.

The recommended junction temperature range is -40°C to 125°C, and the ambient temperature range is -40°C to 85°C.

2 Ordering Information



Package Type⁽¹⁾ J8F: TSOT-23-8 (FC)

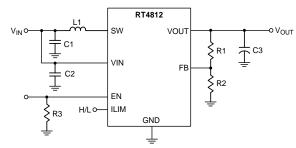
Lead Plating System

G: Richtek Green Policy Compliant⁽²⁾

Note 1.

- Marked with ⁽¹⁾ indicated: Compatible with the current requirements of IPC/JEDEC J-STD-020.
- Marked with ⁽²⁾ indicated: Richtek products are Richtek Green Policy compliant.

6 Simplified Application Circuit



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3 Features

- CMCOT Topology with Small Output Ripple when VIN is close to VOUT Voltage
- Operate from a Single Li-ion Cell: 1.8V to 5.5V
- Adjustable Output Voltage: 1.8V to 5.5V •
- **PSM Operation** •
- Up to 96% Efficiency
- **Boost Current Limit**
- Output Overvoltage Protection
- **Pin-Adjustable Average Output Current-Limit** Threshold (2 Levels)
- Internal Compensation
- **Output Discharge**
- **Output Short Protection**
- **True Load Disconnect**

4 Applications

- Single-Cell Li-Ion, LiFePO4 Smart Phones
- Portable Equipment

5 Marking Information

0L=DNN

0L= : Product Code DNN : Date Code



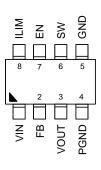
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7 Pin Configuration

(TOP VIEW)



TSOT-23-8 (FC)

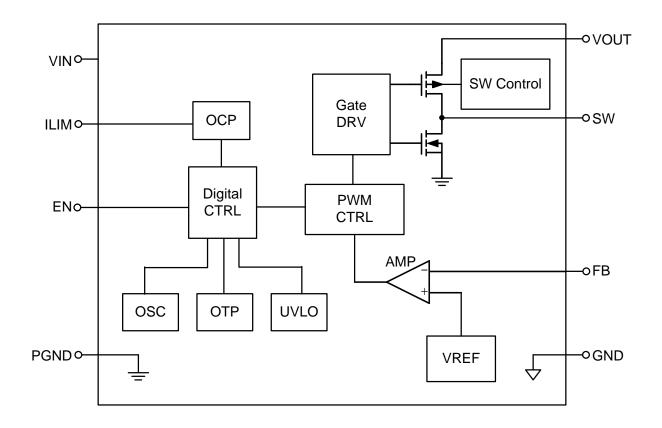
8 Functional Pin Description

Pin No.	Pin Name	Pin Function
1	VIN	Power input. Input capacitor CIN must be placed as close to the IC as possible.
2	FB	Voltage feedback.
3	VOUT	Boost converter output.
4	PGND	Power ground.
5	GND	Analog ground.
6	SW	Switching node.
7	EN	Enable input (1 enabled, 0 disabled), must not be floating.
8	ILIM	Average output current limit control pin. (H/L)

RT4812



9 Functional Block Diagram



10 Absolute Maximum Ratings

(<u>Note 2</u>)

• VIN, FB, ILIM, EN, SW to GND	-0.2V to 6V
VOUT to GND	6.2V
 Power Dissipation, PD @ TA = 25°C 	
TSOT-23-8 (FC)	1.78W
Package Thermal Resistance (<u>Note 3</u>)	
TSOT-23-8 (FC), θJA	56°C/W
TSOT-23-8 (FC), θJC	28°C/W
Lead Temperature (Soldering, 10sec.)	260°C
Junction Temperature	$-65^{\circ}C$ to $150^{\circ}C$
Storage Temperature Range	$-65^{\circ}C$ to $150^{\circ}C$
ESD Susceptibility (<u>Note 4</u>)	
HBM (Human Body Model)	2kV

Note 2. Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions may affect device reliability.

Note 3. θ_{JA} is measured at $T_A = 25^{\circ}C$ on a two-layer Richtek Evaluation Board.

Note 4. Devices are ESD sensitive. Handling precautions are recommended.

11 Recommended Operating Conditions

(<u>Note 5</u>)

٠	Input Voltage Range	1.8V to 5.5V
٠	Output Voltage Range	1.8V to 5.5V
•	Junction Temperature (TJ) Range	–40°C to 125°C
•	Ambient Temperature (TA) Range	–40°C to 85°C

Note 5. The device is not guaranteed to function outside its operating conditions.

12 Electrical Characteristics

$(V_{IN} = 3.6V, T_A = 25^{\circ}C, unless otherwise specified.)$

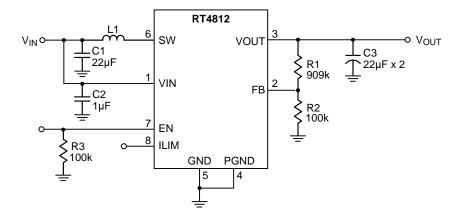
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Supply Input Voltage	VIN	VIN < VOUT - 0.2V	1.8		5.5	V	
Output Voltage	Vout	$V_{IN} < V_{OUT} - 0.2V$	1.8		5.5	V	
Undervoltage-Lockout Rising Threshold	VUVLO_R		1.5	1.65	1.8	V	
Undervoltage-Lockout Falling Threshold	VUVLO_F		1.3	1.55	1.7	V	
Feedback Voltage	Vfb	Force PWM	0.495	0.5	0.505	V	
Output Voltage Accuracy	Vout_acc	$\begin{array}{l} 1.8 \leq V \text{IN} \leq V \text{OUT} - 0.2 V \\ \text{IOUT} = 0 \text{mA} \ (\text{PSM}) \end{array}$	-2		4	%	

RT4812



Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Shutdown Current	ISHDN	EN = 0V		0.1	1	μA
Quiescent Current (Non-Switching Current)	IQ_NSW	Close loop, no load FB = 3V, non-switching current		90		μΑ
Pre-Charge Current	IPRECHG			1		Α
Switching Frequency	fsw	Vout – Vin > 1V		0.5		MHz
Average Output Current Limit	luna.	ILIM = L	1			
Average Output Current Limit	ILIM	ILIM = H	2.1			A
On-Resistance of High-Side MOSFET	Rdson_h	V _{IN} = 5V		45		mΩ
On-Resistance of Low-Side MOSFET	Rdson_L	V _{IN} = 5V		30		mΩ
The FB Pin Input Leakage Current	IFB_LK		-1		1	μΑ
SW Leakage Current	lsw_lk	All switch off			5	μΑ
Line Regulation	VLINE_REG	VIN = 2.7V to 4.5V, VOUT = 5V, IOUT = 1500mA	-2		2	%
Load Regulation	VLOAD_REG	CCM, IOUT < 2A, VIN = 3.6V, VOUT = 5V	-1.5		1.5	%
Output Overvoltage Protection	Vovp		5.8	6	6.2	V
EN Input Voltage Falling Threshold	Ven_f				0.4	V
EN Input Voltage Rising Threshold	Ven_r		1.2			V
EN Input Current	IEN			0.1	1	μΑ
Over-Temperature Protection Threshold	Тотр			160		°C
Over-Temperature Protection Hysteresis	TOTP_HYS			30		°C

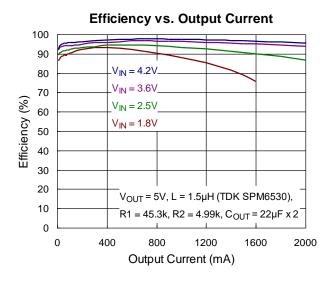
13 Typical Application Circuit



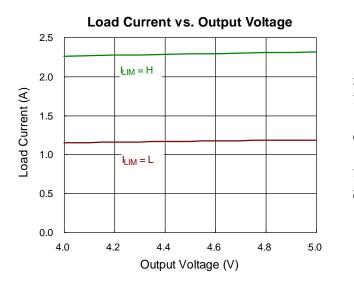


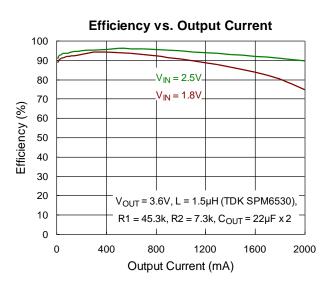
RT4812

14 Typical Operating Characteristics

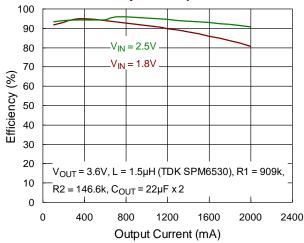


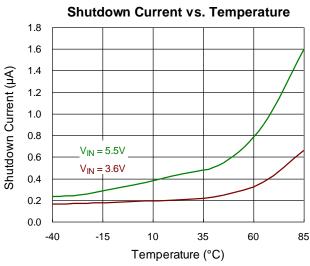
Efficiency vs. Outout Current 100 90 V_{IN} = 4.2V 80 $V_{IN} = 3.7V$ 70 Efficiency (%) V_{IN} = 3.3V 60 $V_{IN} = 2.5V$ 50 V_{IN} = 1.8V 40 30 20 V_{OUT} = 5V, L = 1.5µH (TDK SPM6530), R1 = 909k, 10 R2 = 100k, C_{OUT} = 22µF x 2 0 1600 0 400 800 1200 2000 2400 Outout Current (mA)



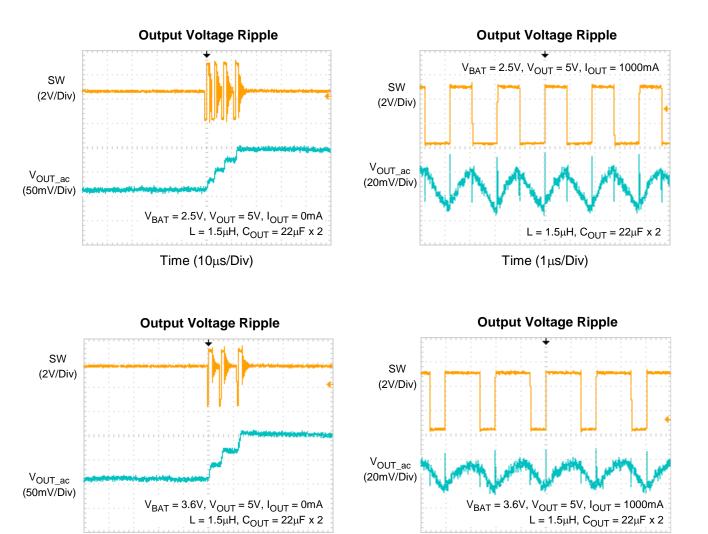


Efficiency vs. Output Current

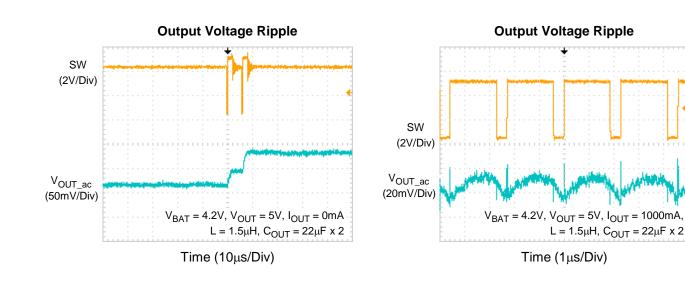








Time (10µs/Div)

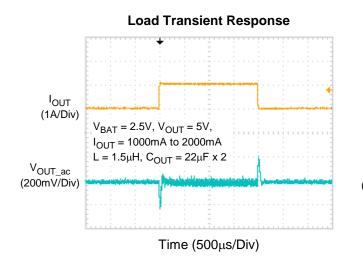


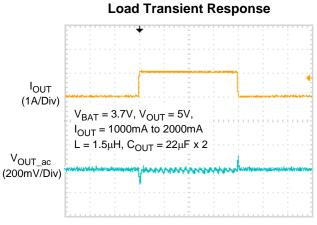
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Time (1µs/Div)

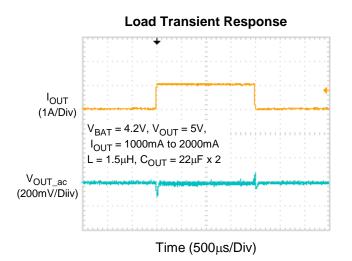








Time (500µs/Div)



15 Operation

The RT4812 combines built-in power transistors, synchronous rectification, and low supply current, providing a compact solution for systems using advanced Li-Ion battery chemistries.

In boost mode, output voltage regulation is guaranteed up to a maximum load current of 2.1A. The quiescent current in Shutdown mode is less than 1μ A, maximizing battery life.

Mode		Depiction	Condition	
	LIN 1	Linear startup 1	VIN > VOUT	
LIN	LIN 2 Linear startup 2		VIN > VOUT	
Soft-Start		Boost soft-start	Vout < Vout(min)	
Boost		Boost mode	Vout = Vout(MIN)	

15.1 LIN State

When VIN is rising, the system enters the LIN state, which consists of two parts: LIN1 provides a maximum charging current of 1A for COUT, and LIN2 provides a maximum charging current of 3A. Additionally, the EN pin is pulled high and VIN is greater than UVLO.

As shown in the figure, if the timeout exceeds the specification, the system will enter fault state.

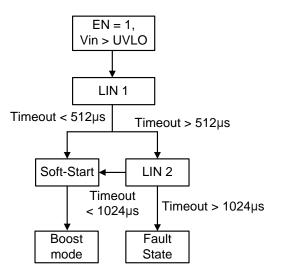


Figure 1. RT4812 State Chart

15.2 Startup and Shutdown State

When VIN is rising and passes through the LIN state, the system will enter the startup state. If EN is pulled low, all functions are turned off in shutdown mode.

15.3 Soft-Start State

The system begins switching in the soft-start state. After the LIN state, the output voltage rises along with the internal reference voltage.





15.4 Fault State

As shown in <u>Figure 1</u>, it will enter the fault state under the following condition:

• The timeout of LIN2 exceeds 1024 µs.

When a fault is triggered, there will be high impedance between the input and output. A restart will occur after 20ms.

15.5 Overcurrent Protection (OCP)

The converter senses the current signal when the high-side P-MOSFET turns on. As a result, the OCP operates with cycle-by-cycle current limitation. If the OCP occurs, the converter holds off the next on pulse until inductor current drops below the OCP limit.

15.6 Over-Temperature Protection (OTP)

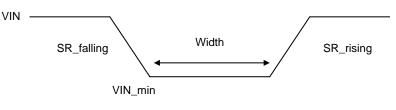
The converter has an over-temperature protection. When the junction temperature exceeds the thermal shutdown rising threshold, the system will latch, and the output voltage will no longer be regulated until the junction temperature drops below the falling threshold.

15.7 Input Voltage POR (Power-On Reset)

The RT4812 implements a Power-on Reset (POR) function. The POR function is used to reset the IC's status to its default settings. The POR function is activated when V_{IN} drops and must meet the POR requirements. The POR function may fail if the VIN patterns do not meet the requirements for a POR event.

The requirements for a POR event are listed below; refer to Figure 2 for the voltage pattern.

- 1. VIN_min < 0.5V
- 2. Width > 20μ s
- 3. SR_rising < 1V/µs



VIN : Input voltage SR_falling : Slew rate for input voltage drop SR_rising : Slew rate for input voltage resume Width : Duration of input voltage drop VIN_min : Minimum voltage

Figure 2. POR Pattern Illustration

16 Application Information

(<u>Note 6</u>)

16.1 Enable

The device can be enabled or disabled by the EN pin. When the EN pin is higher than the logic-high threshold, the device starts operating with soft-start. Once the EN pin is set to low, the device will shut down. In shutdown mode, the converter stops switching, internal control circuitry is turned off, and the load is disconnected from the input. This also means that the output voltage can drop below the input voltage during shutdown.

16.2 Soft-Start State

After successfully completing the LIN state (VOUT \geq VIN - 300mV), the regulator begins switching with a boost valley-current limit of 3500mA. During the soft-start state, VOUT is ramped up by Boost internal loop. If VOUT fails to reach target value during the soft-start period for more than 2ms, a fault condition is declared.

16.3 Output Voltage Setting

The output voltage is adjustable by an external resistive divider. The resistive divider must be connected between VOUT, FB and GND. When the output voltage is regulated properly, the typical value of the voltage at the FB pin is 500mV. The output voltage can be calculated using the equation below:

$$R1 = R2 \times \left(\frac{V_{OUT}}{V_{FB}} - 1\right)$$

16.4 Power Save Mode (PSM)

PSM is used to improve efficiency at light loads. When the output voltage is lower than a set threshold voltage, the converter will operate in PSM.

It raises the output voltage with several pulses until the loop exits PSM.

16.5 Undervoltage-Lockout

The undervoltage-lockout circuit prevents the device from operating incorrectly at low input voltages. It prevents the converter from turning on the power switches under undefined conditions and prevents the battery from deep discharge. The VIN voltage must be greater than 1.65V to enable the converter. During operation, if the VIN voltage drops below 1.55V, the converter is disabled and waits for internal IC default parameter values to be ready until the supply exceeds the UVLO rising threshold. The RT4812 automatically restarts if the input voltage recovers to the input voltage UVLO high level.

16.6 Over-Temperature Protection

The device has a built-in temperature sensor which monitors the internal junction temperature. If the temperature exceeds the threshold, the device stops operating. As soon as the IC temperature has decreased below the threshold with hysteresis, it starts operating again. The built-in hysteresis is designed to avoid unstable operation at IC temperatures near the over-temperature threshold.

16.7 Inductor Selection

The recommended nominal inductance value is 1.5μ H. It is recommended to use an inductor with a dc saturation current \geq 5000mA.



Table 1. List of Inductors							
Manufacturer Series Dimensions (in mm) Saturation Current (mA)							
TDK	SPM6530T	7.1 x 6.5 x 3.0	11500				
Taiyo Yuden	NRS5040T	5.15 x 5.15 x 4.2	6400				

16.8 Input Capacitor Selection

At least a 22μ F capacitor with a rated voltage of 16V for the DC bias input is recommended to improve the transient behavior of the regulator and the EMI behavior of the total power supply circuit for SW. Additionally, at least a 1μ F ceramic capacitor placed as close as possible to the VIN and GND pins of the IC is recommended.

16.9 Output Capacitor Selection

At least two 22µF capacitors are recommended to improve VOUT ripple. Output voltage ripple is inversely proportional to COUT. The output capacitor is selected according to the output ripple, which is calculated as follows:

$$V_{RIPPLE(P-P)} = t_{ON} \times \frac{I_{LOAD}}{C_{OUT}}$$

and

 $t_{ON} = t_{SW} \times D = t_{SW} \times \left(1 - \frac{V_{IN}}{V_{OUT}}\right)$

therefore :

$$C_{OUT} = t_{SW} \times \left(1 - \frac{V_{IN}}{V_{OUT}}\right) \times \frac{I_{LOAD}}{V_{RIPPLE(P-P)}}$$

and

$$t_{SW} = \frac{1}{f_{SW}}$$

The maximum VRIPPLE occurs at minimum input voltage and maximum output load.

16.10 Output Discharge Function

When the EN pin is set to low, the VOUT pin is internally connected to GND for 10ms through an internal discharge N-MOSFET switch. After the 10ms period, the IC will be in a true shutdown state.

This feature prevents residual charge voltages on capacitors connected to the VOUT pins, which may impact proper power-up of the system.

16.11 Valley Current Limit

The RT4812 employs a valley current limit detection scheme to sense inductor current during the off-time. When the loading current is increased such that the loading is above the valley current-limit threshold, the off-time is increased until the current is decreased to the valley-current threshold. The next on-time begins after the current is decreased to the valley-current threshold. On-time is decided by (VOUT - VIN) / VOUT ratio. The output voltage decreases when further loading current increases. The current limit function is implemented by this scheme; refer to Figure 3.

16.12 Average Output Current Limit

The RT4812 features an average output current limit to protect the output terminal. When the load current exceeds the limit, the output current will be clamped.

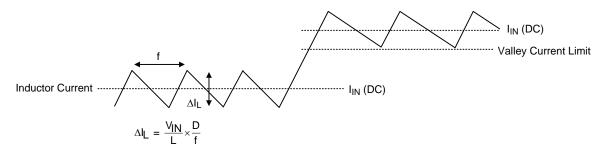


Figure 3. Inductor Current in Current Limit Operation

Table	2. List	of Capa	citor
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Reference	Qty	Part Number	Description	Package	Manufacturer
CIN	1	GRM21BR61C226ME44	22µF/16V/X5R	0805	Murata
COUT	2	GRM21BR61C226ME44	22µF/16V/X5R	0805	Murata

16.13 Thermal Considerations

The junction temperature should never exceed the absolute maximum junction temperature $T_{J(MAX)}$, listed under Absolute Maximum Ratings, to avoid permanent damage to the device. The maximum allowable power dissipation depends on the thermal resistance of the IC package, the PCB layout, the rate of surrounding airflow, and the difference between the junction and ambient temperatures. The maximum power dissipation can be calculated using the following formula:

$\mathsf{P}_{\mathsf{D}(\mathsf{MAX})} = (\mathsf{T}_{\mathsf{J}(\mathsf{MAX})} - \mathsf{T}_{\mathsf{A}}) / \theta_{\mathsf{J}\mathsf{A}}$

where $T_{J(MAX)}$ is the maximum junction temperature, T_A is the ambient temperature, and θ_{JA} is the junction-to-ambient thermal resistance.

For continuous operation, the maximum operating junction temperature indicated under Recommended Operating Conditions is 125°C. The junction-to-ambient thermal resistance, θ_{JA} , is highly package dependent. For a TSOT-23-8 (FC) package, the thermal resistance, θ_{JA} , is 56°C/W on a standard JEDEC 51-7 high effective-thermal-conductivity four-layer test board. The maximum power dissipation at TA = 25°C can be calculated as below:

 $P_{D(MAX)} = (125^{\circ}C - 25^{\circ}C) / (56^{\circ}C/W) = 1.78W$ for a TSOT-23-8 (FC) package.

The maximum power dissipation depends on the operating ambient temperature for the fixed T_J(MAX) and the thermal resistance, θ_{JA} . The derating curve in <u>Figure 4</u> allows the designer to see the effect of rising ambient temperature on the maximum power dissipation.



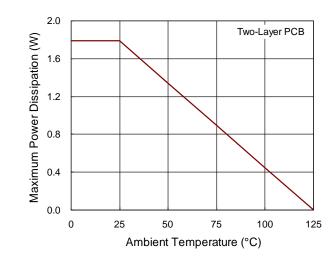


Figure 4. Derating Curve of Maximum Power Dissipation

16.14 Layout Considerations

The PCB layout is an important step to maintain the high performance of the RT4812.

Both the high current and the fast switching nodes require careful attention to the PCB layout to ensure the robustness of the RT4812.

Improper layout might result in poor line or load regulation, ground and output voltage shifts, stability issues, unsatisfactory EMI behavior, or reduced efficiency. For the best performance of the RT4812, the following PCB layout guidelines must be strictly followed:

- Input/output capacitors must be placed as close as possible to the input/output pins.
- The SW pin should be connected to the Inductor with a wide and short trace, and sensitive components should be kept away from this trace.
- The feedback divider should be placed as close as possible to the FB pin.

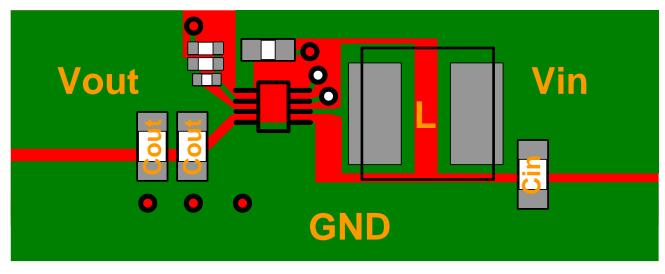
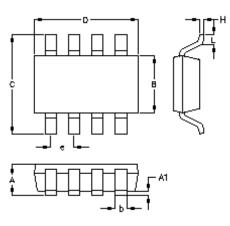


Figure 5. PCB Layout Guide

Note 6. The information provided in this section is for reference only. The customer is solely responsible for designing, validating, and testing any applications incorporating Richtek's product(s). The customer is also responsible for applicable standards and any safety, security, or other requirements.

17 Outline Dimension

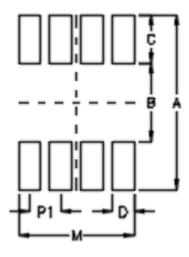


Symbol	Dimensions I	n Millimeters	Dimensions In Inches		
Symbol	Min	Мах	Min	Max	
A	0.700	1.000	0.028	0.039	
A1	0.000	0.100	0.000	0.004	
В	1.397	1.803	0.055	0.071	
b	0.220	0.380	0.009	0.015	
С	2.591	3.000	0.102	0.118	
D	2.692	3.099	0.106	0.122	
е	0.585	0.715	0.023	0.028	
н	0.080	0.254	0.003	0.010	
L	0.300	0.610	0.012	0.024	

TSOT-23-8 (FC) Surface Mount Package



18 Footprint Information

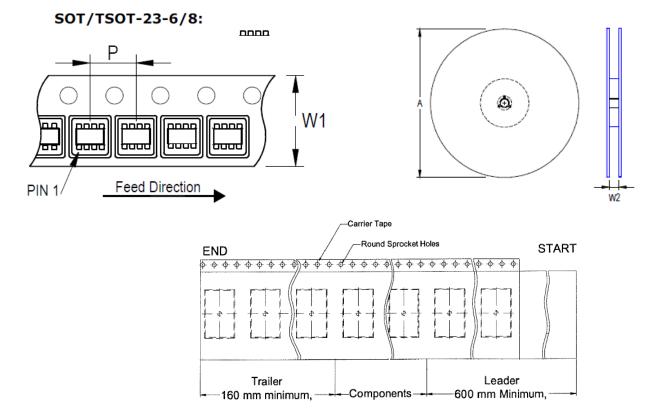


Deekogo	Number		Talaranaa					
Package	of Pin	P1	А	В	С	D	М	Tolerance
TSOT-28/TSOT-28(FC)/SOT-28	8	0.65	3.60	1.60	1.00	0.45	2.40	±0.10

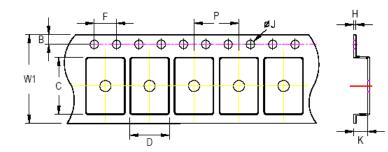
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19 Packing Information

19.1 Tape and Reel Data



Package Type	Tape Size	Pocket Pitch	Reel Si	ze (A)	Units	Trailer	Leader	Reel Width (W2)
	(W1) (mm)	(P) (mm)	(mm)	(in)	per Reel	(mm)	(mm)	Min./Max. (mm)
TSOT-23-8	8	4	180	7	3,000	160	600	8.4/9.9



C, D, and K are determined by component size. The clearance between the components and the cavity is as follows:

- For 8mm carrier tape: 0.5mm max.

Tapa S	70	W1	F	C	E	3	F	=	Ø	ຢງ	ł	<	Н
Tape S	ze	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Max.
8mm		8.3mm	3.9mm	4.1mm	1.65mm	1.85mm	3.9mm	4.1mm	1.5mm	1.6mm	1.0mm	1.2mm	0.6mm





19.2 Tape and Reel Packing

Step	Photo/Description	Step	Photo/Description
1		4	
	Reel 7"		3 reels per inner box Box A
2		5	
	HIC & Desiccant (1 Unit) inside		12 inner boxes per outer box
3		6	RCHTEK To Zen Tran
	Caution label is on backside of Al bag		Outer box Carton A

Container	R	leel		Box		Carton			
Package	Size	Units	Item	Reels	Units	Item	Boxes	Unit	
T00T 00 0		0.000	Box A	3	9,000	Carton A	12	108,000	
TSOT-23-8	7" 3,000		Box E	1	3,000	For Co	mbined or Partial I	Reel.	

19.3 Packing Material Anti-ESD Property

Surface Resistance	Aluminum Bag	Reel	Cover tape	Carrier tape	Tube	Protection Band
Ω/cm^2	10 ⁴ to 10 ¹¹					

Richtek Technology Corporation

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20 Datasheet Revision History

Version	Date	Description	Item
10	2024/8/20	Modify	General Description on page 1 -Added Temperature range Ordering Information on page 1 -Modified description Electrical Characteristics on page 5, 6 -Updated description and symbol Application Information on page 16 -Added the declaration Footprint Information on page 18 -Added footprint information Packing Information on page 19, 20, 21 -Added packing information

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